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November 2013

## FCP25N60N

## N-Channel SupreMOS® MOSFET

**600 V, 25 A, 125 m** $\Omega$ 

#### **Features**

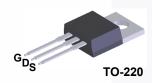
- $R_{DS(on)} = 107 \text{ m}\Omega \text{ (Typ.)} @ V_{GS} = 10 \text{ V, } I_D = 12.5 \text{ A}$
- Ultra Low Gate Charge (Typ. Q<sub>q</sub> = 57 nC)
- Low Effective Output Capacitance (Typ. C<sub>oss(eff.)</sub> = 262 pF)
- · 100% Avalanche Tested
- · RoHS Compliant

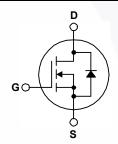
## **Application**

- · Solar Inverter
- · AC-DC Power Supply

### **Description**

The SupreMOS® MOSFET is Fairchild Semiconductor's next generation of high voltage super-junction (SJ) technology employing a deep trench filling process that differentiates it from the conventional SJ MOSFETs. This advanced technology and precise process control provides lowest Rsp on-resistance, superior switching performance and ruggedness. SupreMOS MOSFET is suitable for high frequency switching power converter applications such as PFC, server/telecom power, FPD TV power, ATX power, and industrial power applications.





#### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FCP25N60N_F102	Unit
V <sub>DSS</sub>	Drain to Source Voltage		600	V
V <sub>GSS</sub>	Gate to Source Voltage		±30	V
	Drain Current	- Continuous (T <sub>C</sub> = 25°C)	25	^
ID	Drain Current	- Continuous (T <sub>C</sub> = 100°C)	16	A
I <sub>DM</sub>	Drain Current	- Pulsed (Note	1) 75	Α
E <sub>AS</sub>	Single Pulsed Avalanche	Energy (Note	2) 861	mJ
I <sub>AR</sub>	Avalanche Current	(Note	1) 8.3	Α
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)		1) 2.2	mJ
dv/dt	Peak Diode Recovery dv/d	it (Note	3) 20	V/ns
av/at	MOSFET dv/dt		100	V/IIS
D	Dower Discinction	(T <sub>C</sub> = 25°C)	216	W
P <sub>D</sub> Power Dissipation		<ul> <li>Derate Above 25°C</li> </ul>	1.72	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C

#### **Thermal Characteristics**

Symbol	Parameter	FCP25N60N_F102	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.58	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max. 62.5		-0/00

## **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCP25N60N_F102	FCP25N60N	TO-220	Tube	N/A	N/A	50 units

## **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}, T_J = 25^{\circ}\text{C}$	600	-	-	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 1 mA, Referenced to 25°C	-	0.74	-	V/°C
1	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 480 V, V <sub>GS</sub> = 0 V	-	-	10	
I <sub>DSS</sub> Zero G	Zero Gate voltage Drain Current	$V_{DS} = 480 \text{ V}, T_{J} = 125^{\circ}\text{C}$	-	-	100	μΑ
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>GS</sub> = ±30 V, V <sub>DS</sub> = 0 V	-	-	±100	nA

#### **On Characteristics**

V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	2.0	-	4.0	V
R <sub>DS(on)</sub>	Static Drain to Source On Resistance	$V_{GS}$ = 10 V, $I_{D}$ = 12.5 A	-	0.107	0.125	Ω

#### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	1001/1/	-	2520	3352	pF
Coss	Output Capacitance	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, f = 1 MHz		103	137	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			3.2	5	pF
C <sub>oss</sub>	Output Capacitance	$V_{DS} = 380 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	55	-	pF
C <sub>oss</sub> eff.	Effective Output Capacitance	$V_{DS} = 0 \text{ V to } 480 \text{ V}, V_{GS} = 0 \text{ V}$	-	262	-	pF
Q <sub>g(tot)</sub>	Total Gate Charge at 10V	V <sub>DS</sub> = 380 V, I <sub>D</sub> = 12.5 A,	-	57	74	nC
$Q_{gs}$	Gate to Source Gate Charge	V <sub>GS</sub> = 10 V	-	10	-	nC
Q <sub>gd</sub>	Gate to Drain "Miller" Charge	(Note 4)	-	18	-	nC
ESR	Equivalent Series Resistance (G-S)	f = 1 MHz	-	1	-	Ω

#### **Switching Characteristics**

	_					
t <sub>d(on)</sub>	Turn-On Delay Time		-	21	52	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = 380 \text{ V}, I_{D} = 12.5 \text{ A},$	-	22	54	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS}$ = 10 V, $R_{G}$ = 4.7 $\Omega$	-/	68	146	ns
t <sub>f</sub>	Turn-Off Fall Time	(Not	- 4)	5	20	ns

#### **Drain-Source Diode Characteristics**

I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current			-	25	Α
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	75	Α
$V_{SD}$	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 12.5 A	-	-	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 12.5 A,	-	370	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	$dI_F/dt = 100 A/\mu s$	-	7	-	μС

#### Notes

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2.  $I_{AS}$  = 8.3 A,  $R_{G}$  = 25  $\Omega$ , starting  $T_{J}$  = 25°C.
- 3. I  $_{SD} \leq$  25 A, di/dt  $\leq$  200 A/µs, V  $_{DD} \leq$  380 V, starting T  $_{J}$  = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

## **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

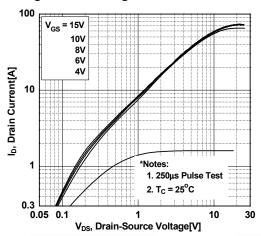


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

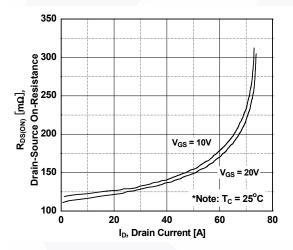
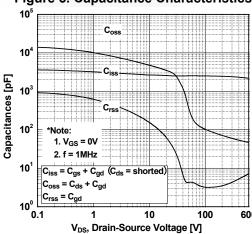


Figure 5. Capacitance Characteristics



**Figure 2. Transfer Characteristics** 

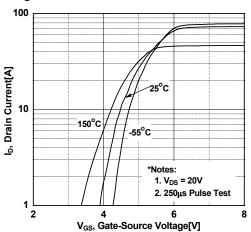


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

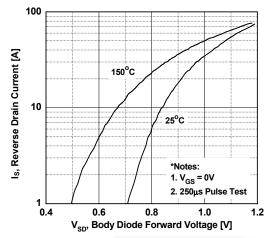
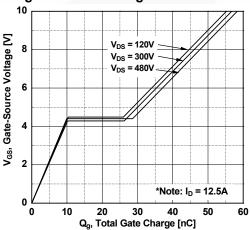


Figure 6. Gate Charge Characteristics



## **Typical Performance Characteristics** (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

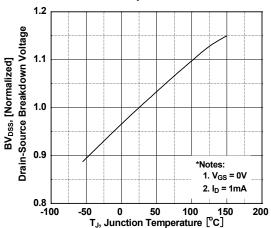


Figure 8. On-Resistance Variation vs. Temperature

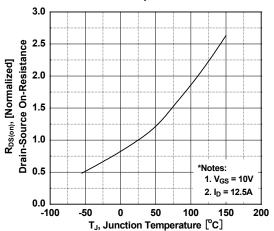


Figure 9. Maximum Safe Operating Area

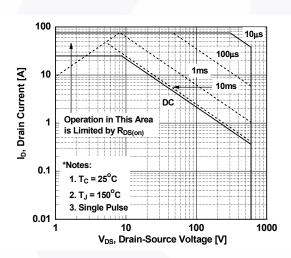


Figure 10. Maximum Drain Current vs. Case Temperature

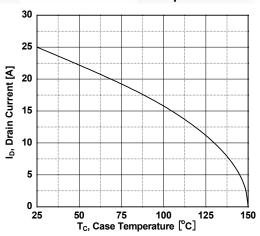
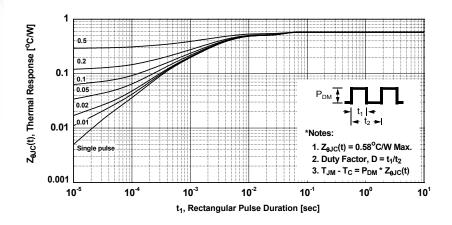


Figure 11. Transient Thermal Response Curve



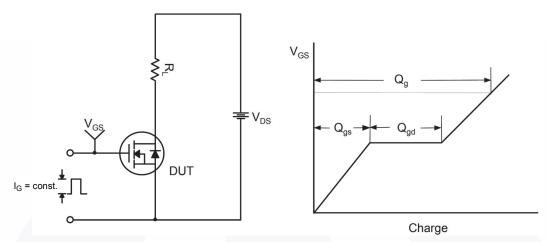


Figure 12. Gate Charge Test Circuit & Waveform

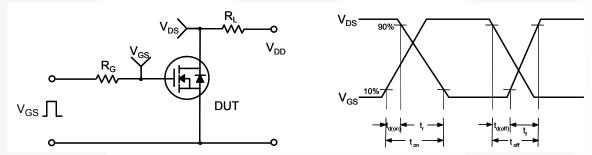


Figure 13. Resistive Switching Test Circuit & Waveforms

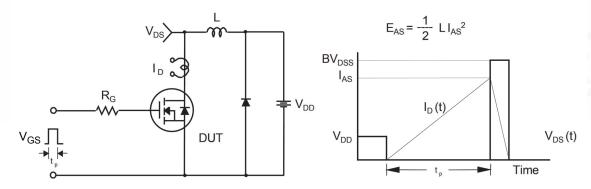


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

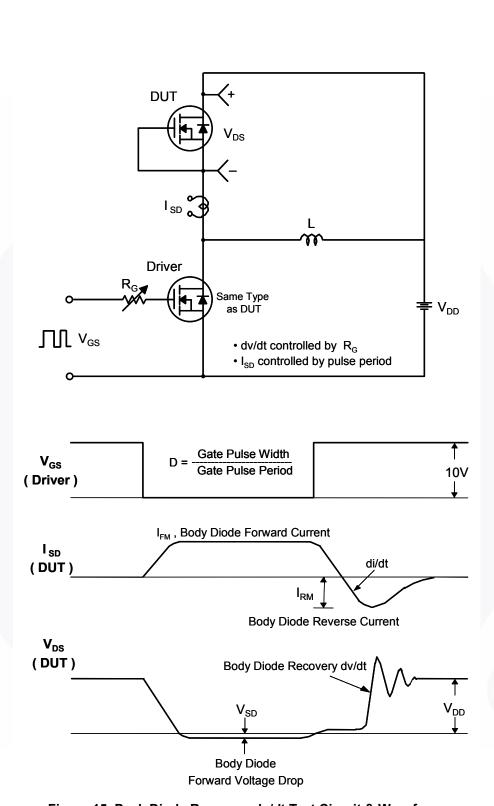


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

#### **Mechanical Dimensions**

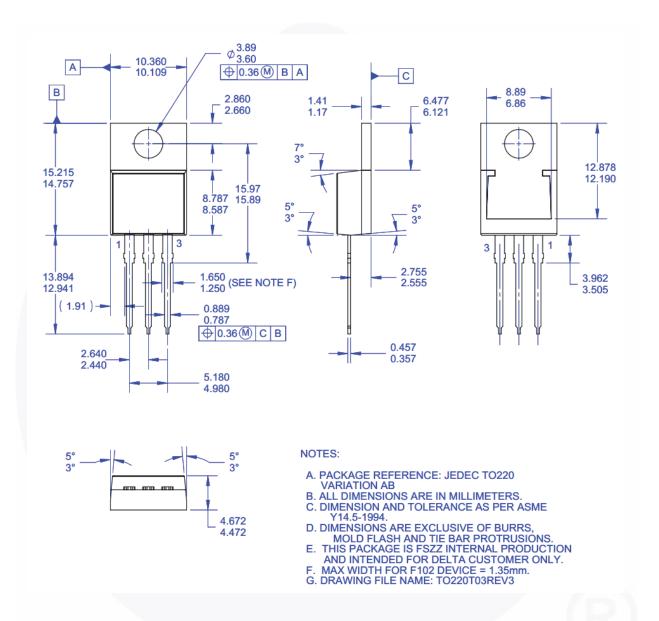


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB (Delta)

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